Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS303PX.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- · High collector current gain (hFE) at high IC
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

3. Applications

- DC-to-DC conversion
- MOSFET gate driving
- Motor control
- · Charging circuits
- · Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	30	V
Ic	collector current		-	-	5.1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	10.2	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	31	44	mΩ



30 V, 5.1 A NPN low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		в
3	В	base	3 2 1 SOT89	E sym042

6. Ordering information

Table 3. Ordering information

Type number Package					
	Name	Description	Version		
PBSS303NX		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS303NX	%5D

[1] % = placeholder for manufacturing site code

30 V, 5.1 A NPN low VCEsat transistor

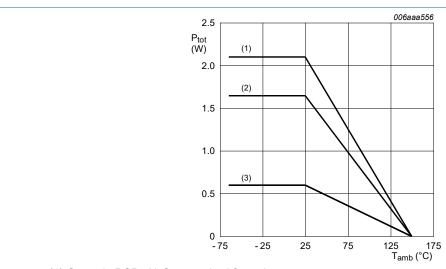
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	30	V
V _{CEO}	collector-emitter voltage	open base		-	30	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
Ic	collector current			-	5.1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	10.2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.6	W
			[2]	-	1.65	W
			[3]	-	2.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint. [3]



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. **Power derating curves**

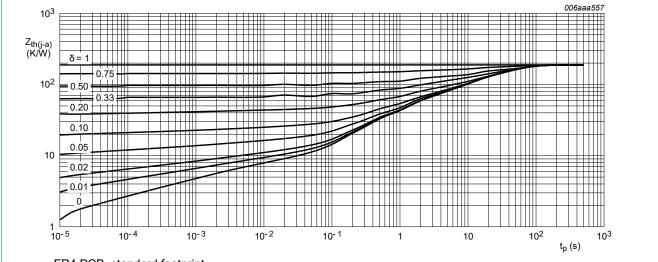
30 V, 5.1 A NPN low VCEsat transistor

9. Thermal characteristics

Table 6. Thermal characteristics

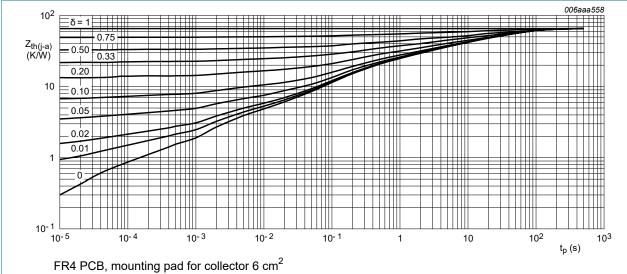
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uiy-a)	thermal resistance from		[1]	-	-	208	K/W
	junction to ambient		[2]	-	-	76	K/W
			[3]	-	-	60	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



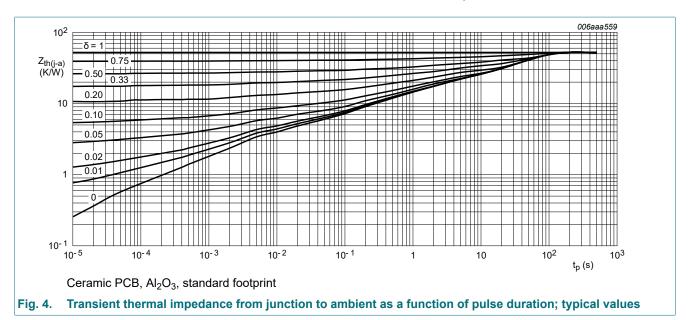
FR4 PCB, standard footprint

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 2.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 3.

30 V, 5.1 A NPN low VCEsat transistor



5/14

30 V, 5.1 A NPN low VCEsat transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{СВО}	collector-base cut-off	V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{ЕВО}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	480	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	460	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	250	430	-	
		V_{CE} = 2 V; I_{C} = 4 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	360	-	
		V_{CE} = 2 V; I_{C} = 6 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	180	270	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 0.5 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	20	30	mV
		I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	40	60	mV
		I_C = 1 A; I_B = 10 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	60	90	mV
		I_C = 2 A; I_B = 40 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	80	110	mV
		I_C = 4 A; I_B = 200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	125	175	mV
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	120	170	mV
		I_C = 4 A; I_B = 40 mA; pulsed; $t_p \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	160	250	mV
		I_C = 5.1 A; I_B = 255 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	150	220	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 4 A; I_B = 200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	31	44	mΩ
		I_C = 4 A; I_B = 40 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	40	63	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.81	0.9	V
		I_C = 4 A; I_B = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.95	1.05	V
I_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.75	0.85	V
d	delay time	V _{CC} = 12.5 V; I _C = 3 A; I _{Bon} = 0.15 A;	-	15	-	ns
r	rise time	I _{Boff} = -0.15 A; T _{amb} = 25 °C	-	50	-	ns
on	turn-on time		-	65	-	ns
s	storage time		-	305	-	ns
f	fall time		-	70	-	ns
off	turn-off time]	-	375	-	ns

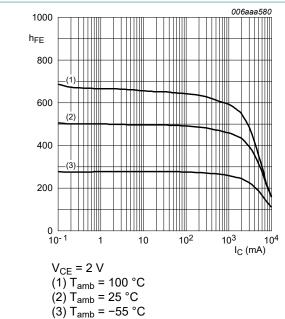
PBSS303NX

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30 V, 5.1 A NPN low VCEsat transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 0.1 A; f = 100 MHz; T_{amb} = 25 °C	-	130	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$	-	60	100	pF



DC current gain as a function of collector current; typical values

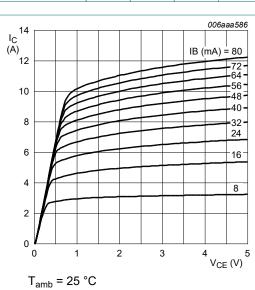
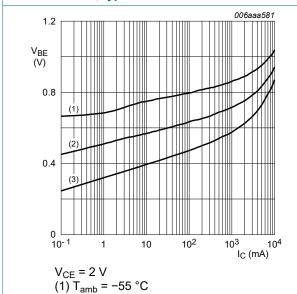
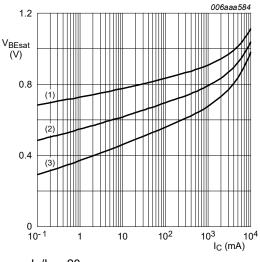


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



(2) T_{amb} = 25 °C (3) T_{amb} = 100 °C Fig. 7. Base-emitter voltage as a function of collector

current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1) $T_{\rm amb} = -55~{\rm ^{\circ}C}$ (2) $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3) $T_{\rm amb} = 100~{\rm ^{\circ}C}$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

Fig. 5.

30 V, 5.1 A NPN low VCEsat transistor

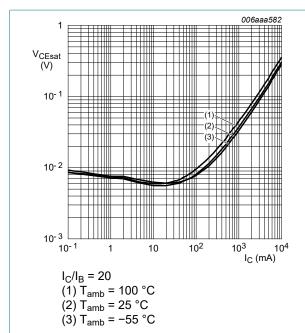


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

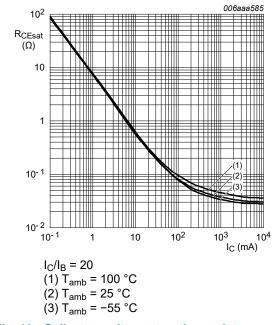


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

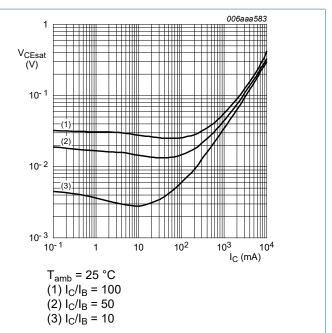


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

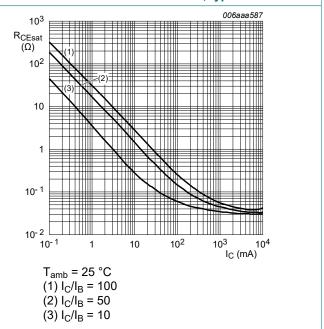


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

30 September 2025

30 V, 5.1 A NPN low VCEsat transistor

11. Test information

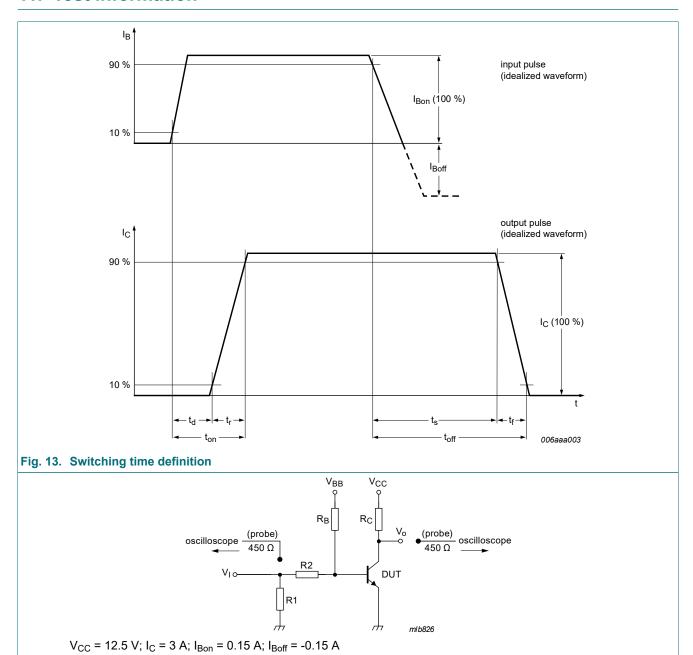
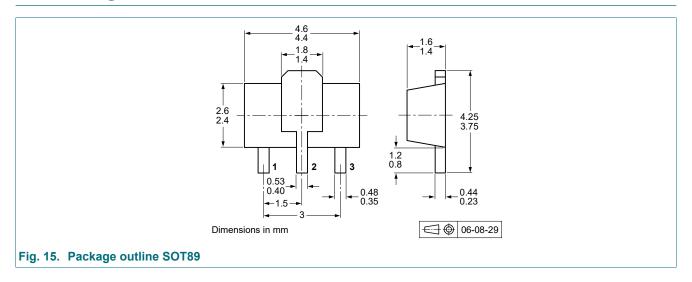


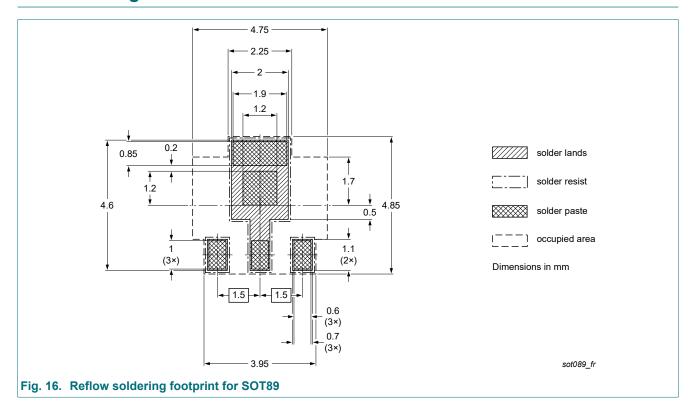
Fig. 14. Test circuit for switching times

30 V, 5.1 A NPN low VCEsat transistor

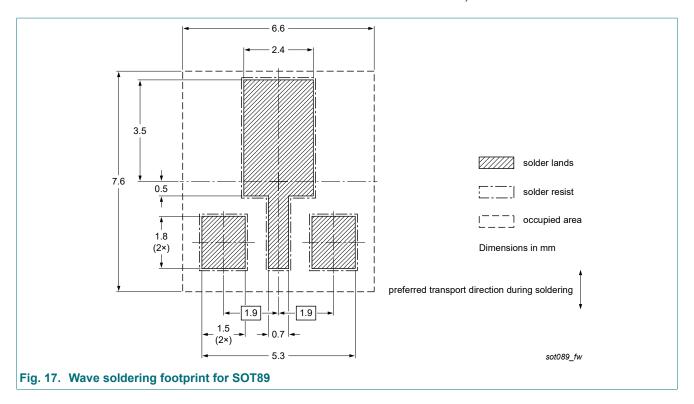
12. Package outline



13. Soldering



30 V, 5.1 A NPN low VCEsat transistor



11 / 14

30 V, 5.1 A NPN low VCEsat transistor

14. Revision history

Table 8. Revision history

Table 6. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS303NX v.4	20250930	Product data sheet	-	PBSS303NX v.3			
Modifications:		 Product(s) changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s). 					
PBSS303NX v.3	20240219	Product data sheet	-	PBSS303NX_2			
PBSS303NX_2	20091120	Product data sheet	-	PBSS303NX_1			
PBSS303NX_1	20060823	Product data sheet	-	-			

30 September 2025

30 V, 5.1 A NPN low VCEsat transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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30 V, 5.1 A NPN low VCEsat transistor

Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
	Marking	
8.	Limiting values	3
9.	Thermal characteristics	4
10.	. Characteristics	6
11.	. Test information	9
12.	. Package outline	10
	Soldering	
14.	Revision history	12
	Legal information	
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